## SPTECH Silicon PNP Power Transistor

### 2SB817

#### DESCRIPTION

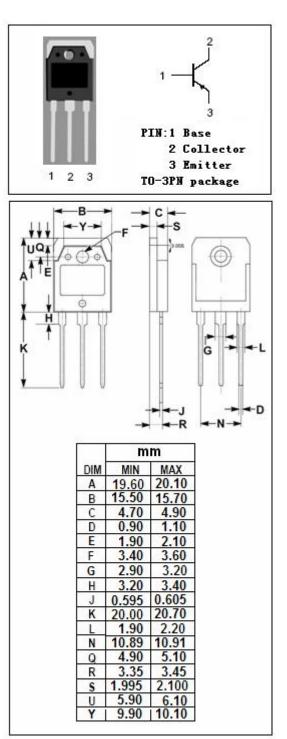
- Collector-Emitter Breakdown Voltage-
- : V<sub>(BR)CEO</sub>= -140V(Min)
- Good Linearity of h<sub>FE</sub>
- High Current Capability
- Wide Area of Safe Operation
- Complement to Type 2SD1047

### **APPLICATIONS**

• Recommend for 60W audio frequency amplifier output stage applications

#### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	-160	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	-140	V	
V <sub>EBO</sub>	Emitter-Base Voltage	-6	V	
Ic	Collector Current-Continuous	-12	А	
I <sub>CP</sub>	Collector Current-Pulse	-15	А	
Pc	Collector Power Dissipation @ $T_c=25^{\circ}C$	100	W	
TJ	Junction Temperature	150	°C	
T <sub>stg</sub>	Storage Temperature Range	-40~150	°C	



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### **ELECTRICAL CHARACTERISTICS**

#### T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	Ic= -30mA ; R <sub>BE</sub> =∞	-140			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = -5mA; I <sub>E</sub> = 0	-160			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -5mA; I <sub>C</sub> = 0	-6			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -5.0A; I <sub>B</sub> = -0.5A			-2.5	V
$V_{\text{BE(on)}}$	Base -Emitter On Voltage	I <sub>C</sub> = -1A ; V <sub>CE</sub> = -5V			-1.5	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = -80V ; I <sub>E</sub> =0			-100	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -4V; I <sub>C</sub> =0			-100	μA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -1A ; V <sub>CE</sub> = -5V	60		200	
h <sub>FE-2</sub>	DC Current Gain	Ic= -6A ; Vce= -5V	20			
Сов	Output Capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> = -10V;f <sub>test</sub> = 1.0MHz		300		pF
fT	Current-Gain—Bandwidth Product	Ic=-1A ; Vce= -5V		15		MHz

Switching times

t <sub>on</sub>	Turn-on Time		0.25	μs
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = -1A ,R <sub>L</sub> = 20 Ω , I <sub>B1</sub> = -I <sub>B2</sub> = -0.1A,V <sub>CC</sub> =-20V	1.61	μs
t <sub>f</sub>	Fall Time		0.53	μs

### • h<sub>FE-1</sub> Classifications

D	Е
60-120	100-200

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